

09965937 092801
108260 46659660

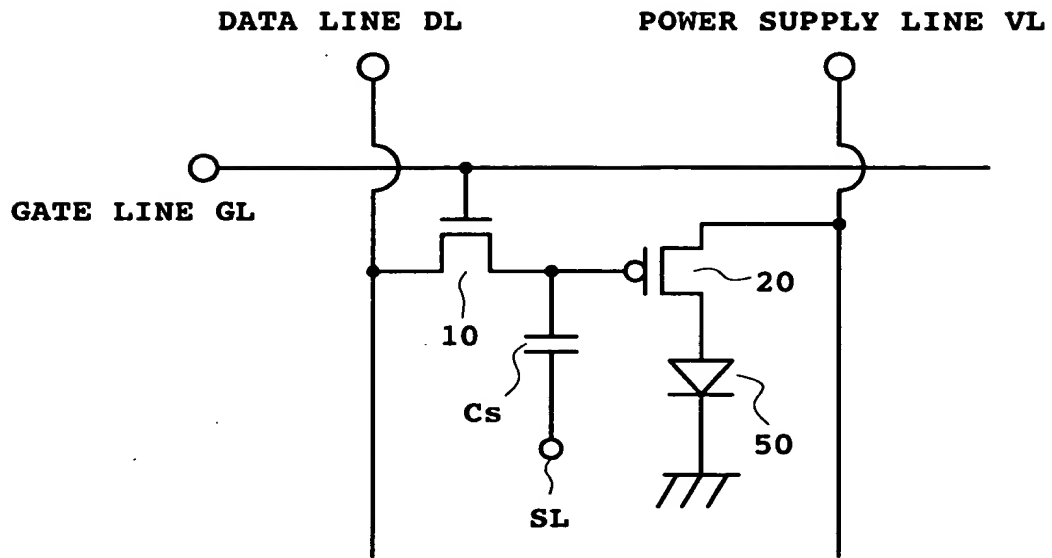


Fig.1

TOP SECRET 4459660

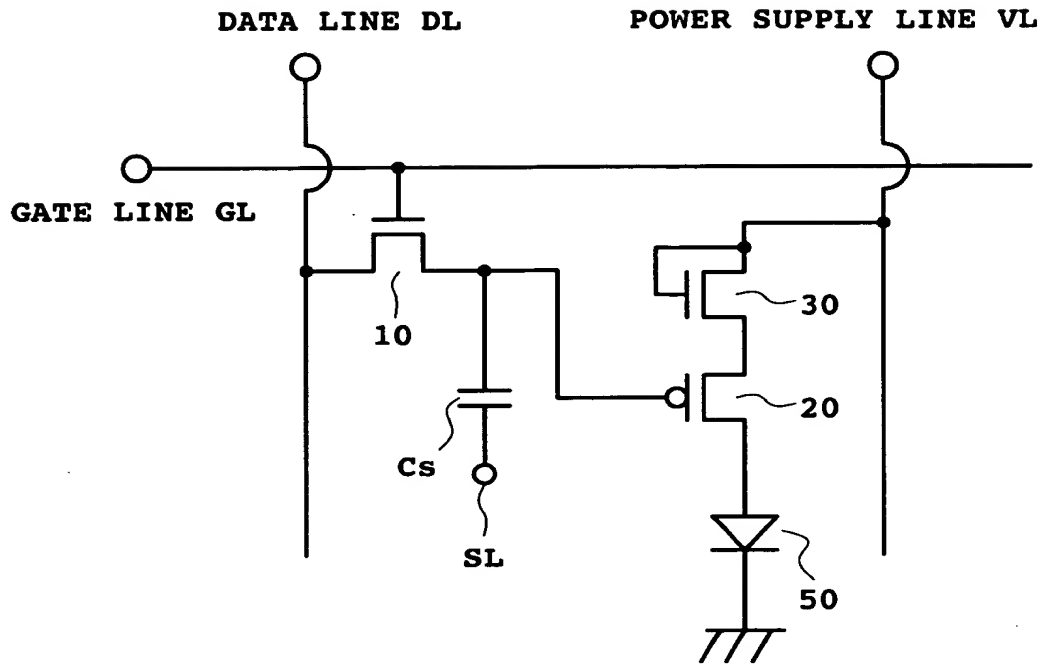


Fig.2

108260" 4E659660

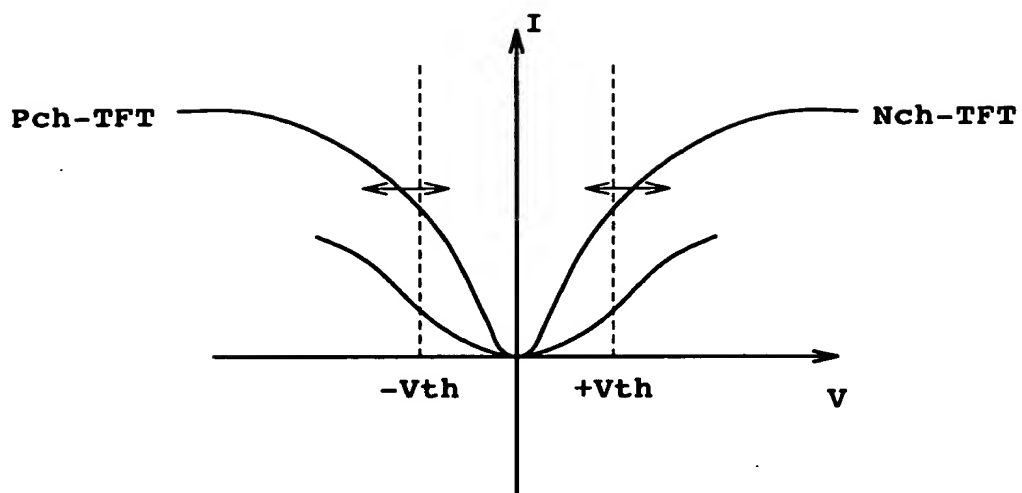


Fig.3

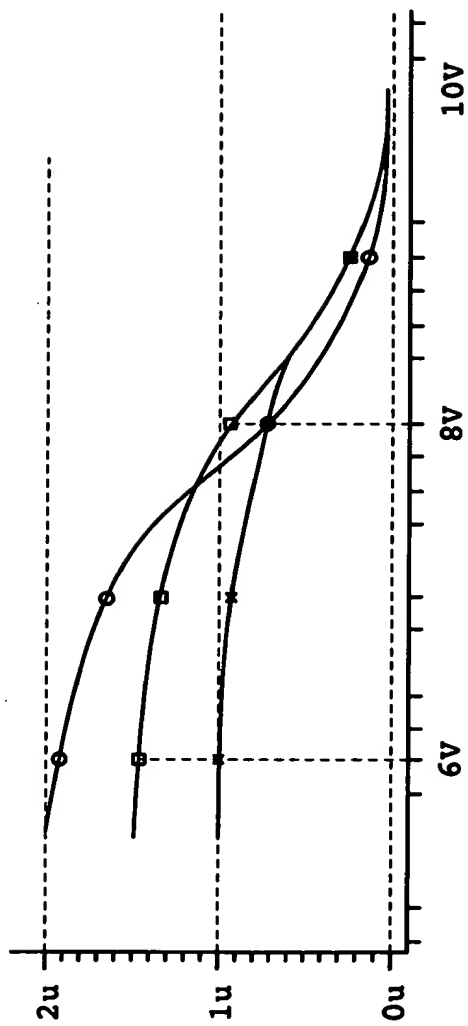


Fig. 4A

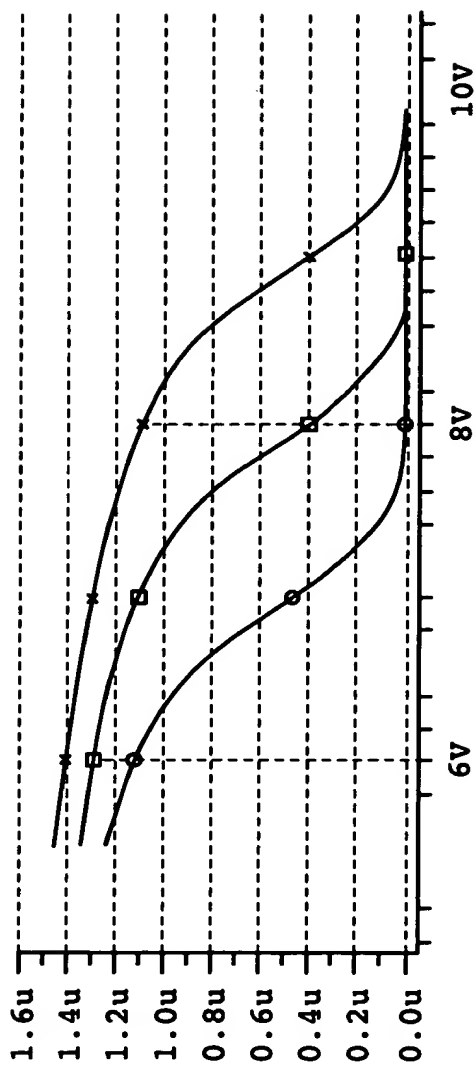


Fig. 4B

TOP SECRET 12659660

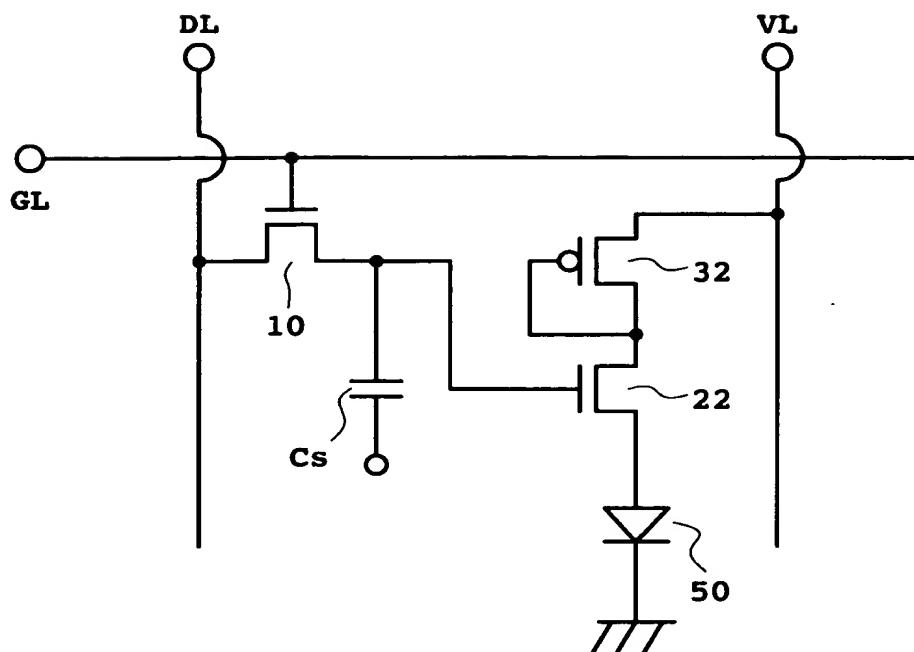


Fig.5

TOP SECRET 4659660

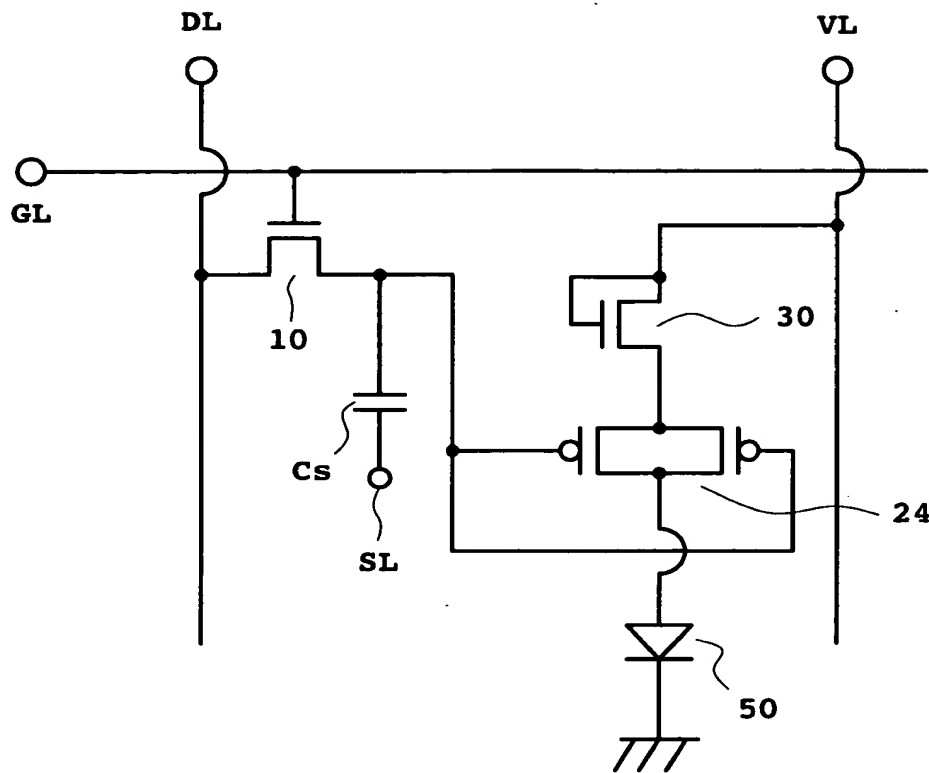


Fig.6

TOP SECRET 42659660

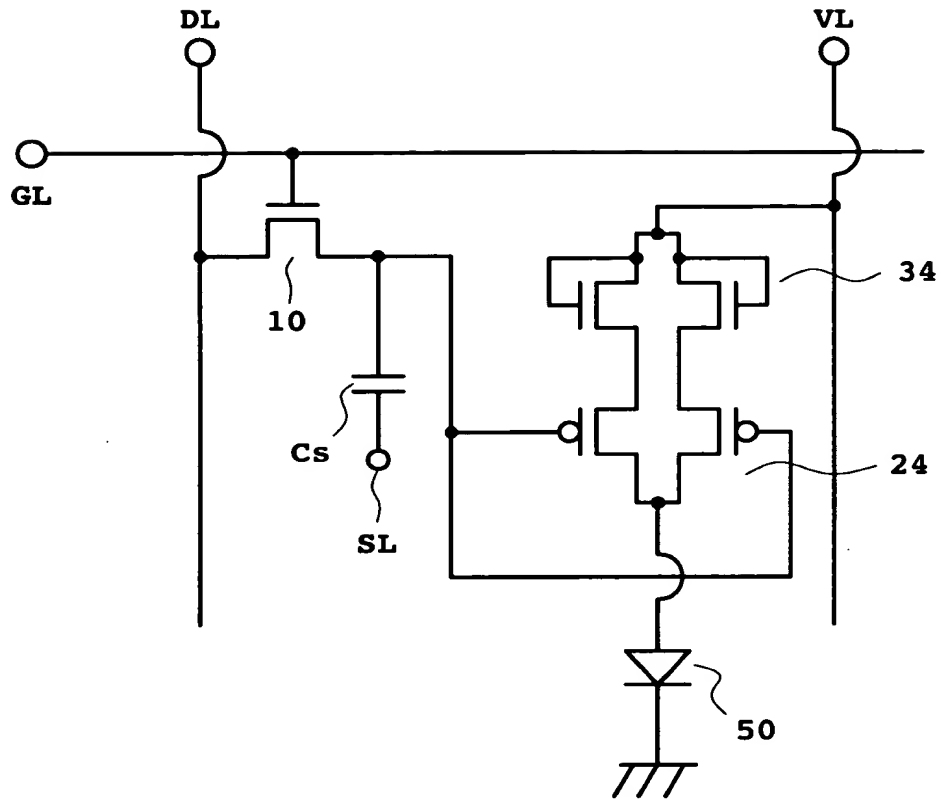


Fig.7

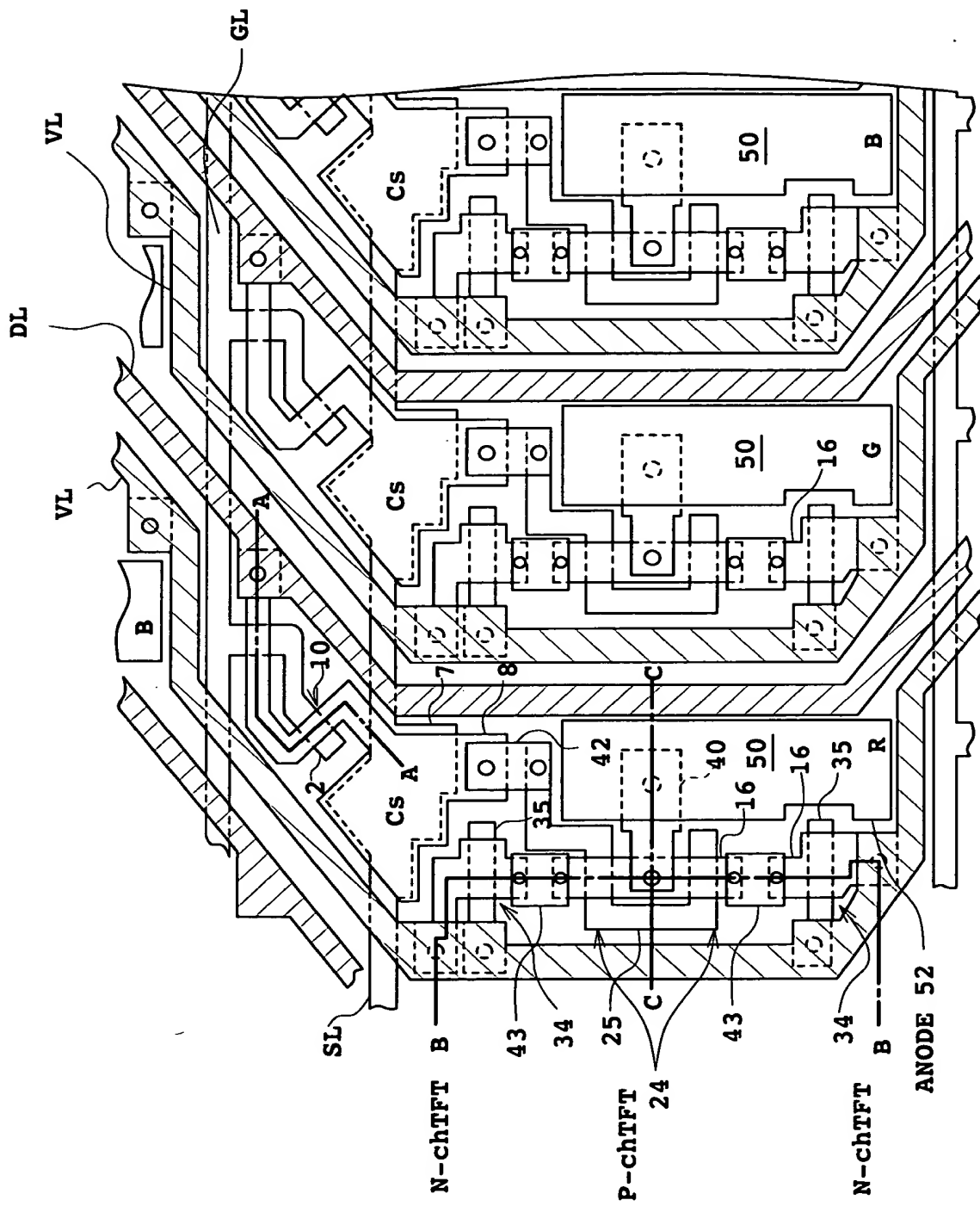


Fig. 8

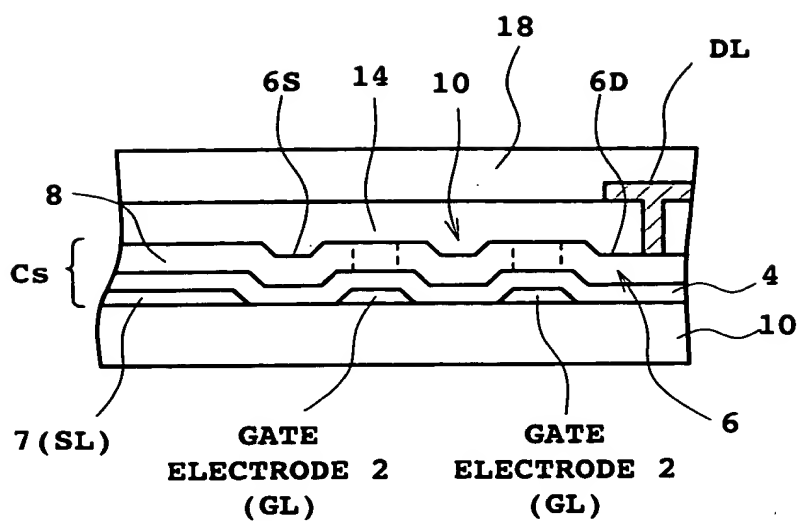


Fig. 9A

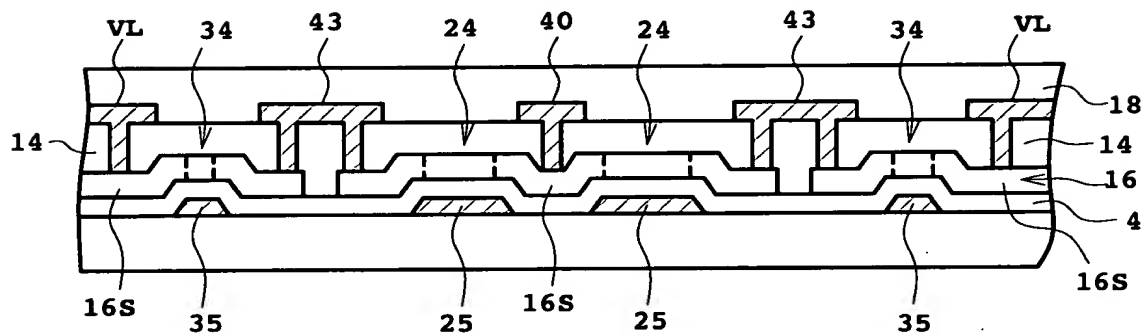


Fig. 9B

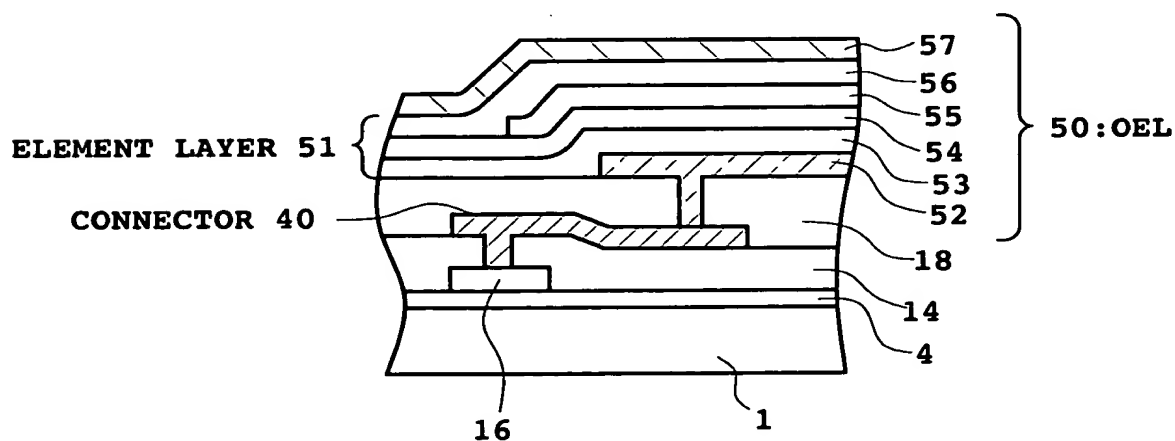
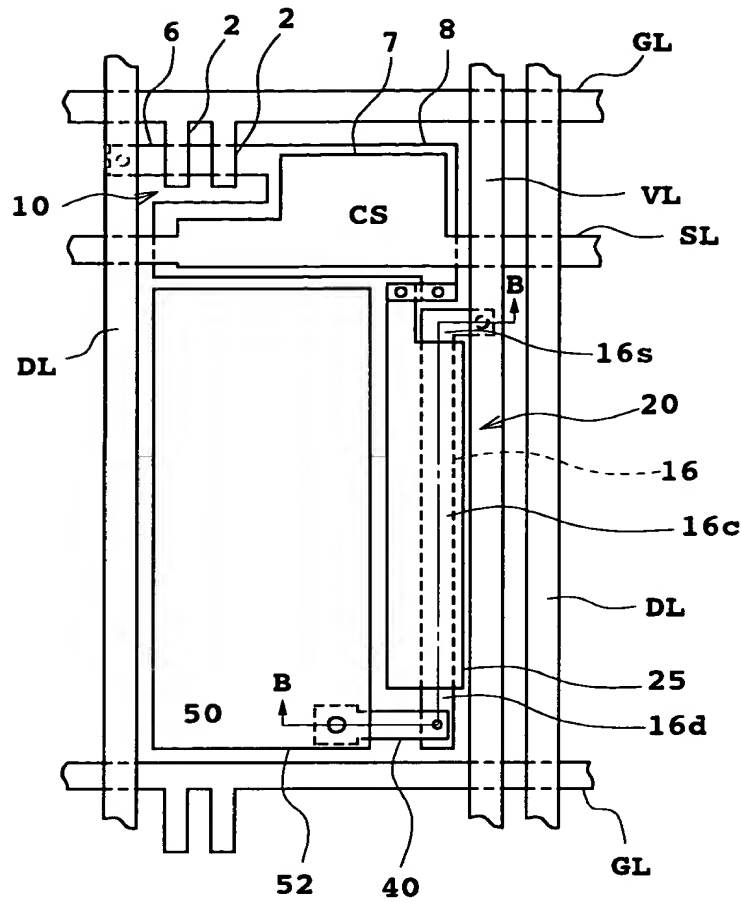


Fig. 9C

SCAN DIRECTION OF LASER ANNEAL



A detailed cross-sectional diagram of a semiconductor device. The base layer is labeled 1. Above it are several other layers: 4, 14, and 18. A central component is labeled 20, which includes a hatched rectangular block 25. This component is flanked by two vertical structures labeled 16s and 16d, which sit on a common base 16. A label VL points to a horizontal layer above the central assembly. To the right, there is a complex stack of layers labeled 51, which includes sub-layers 52, 53, 54, 55, 56, and 57. A bracket groups these layers under the label 51. Other labels include 61 pointing to a top surface layer, and 40 pointing to a specific feature on the right side of the main body.

Fig. 10B

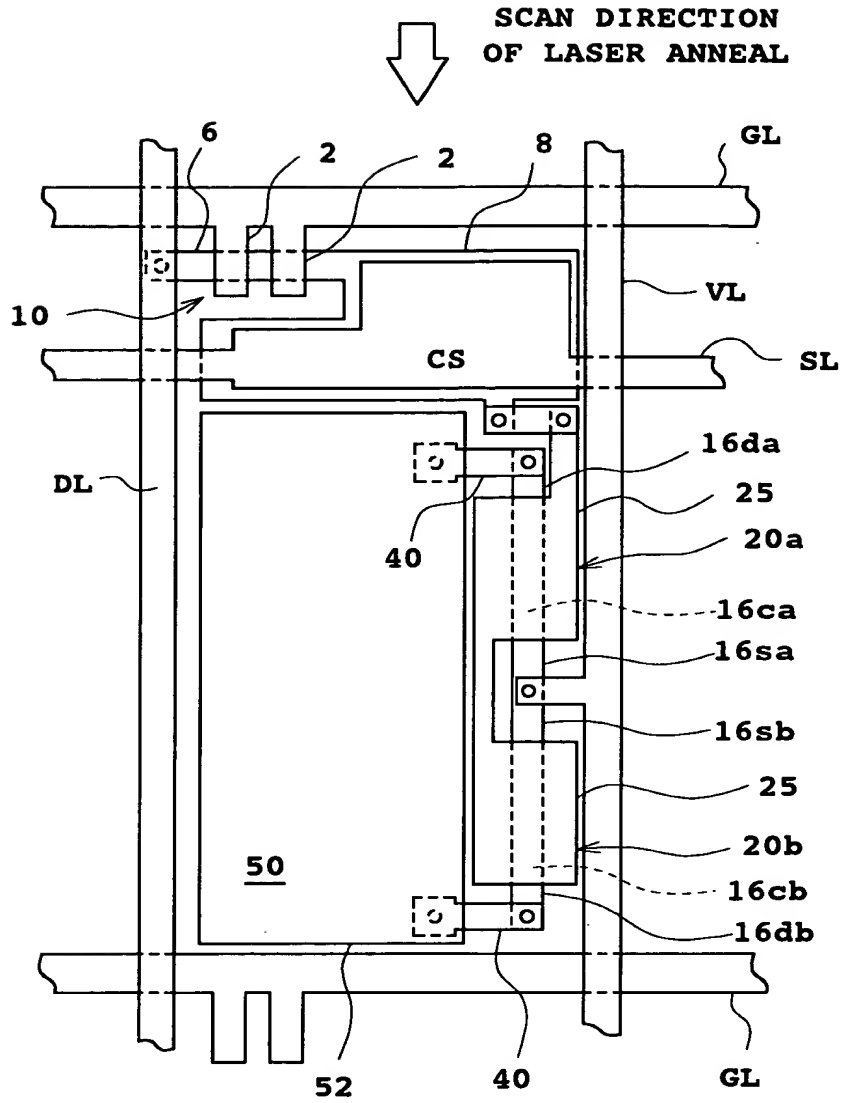


Fig.11

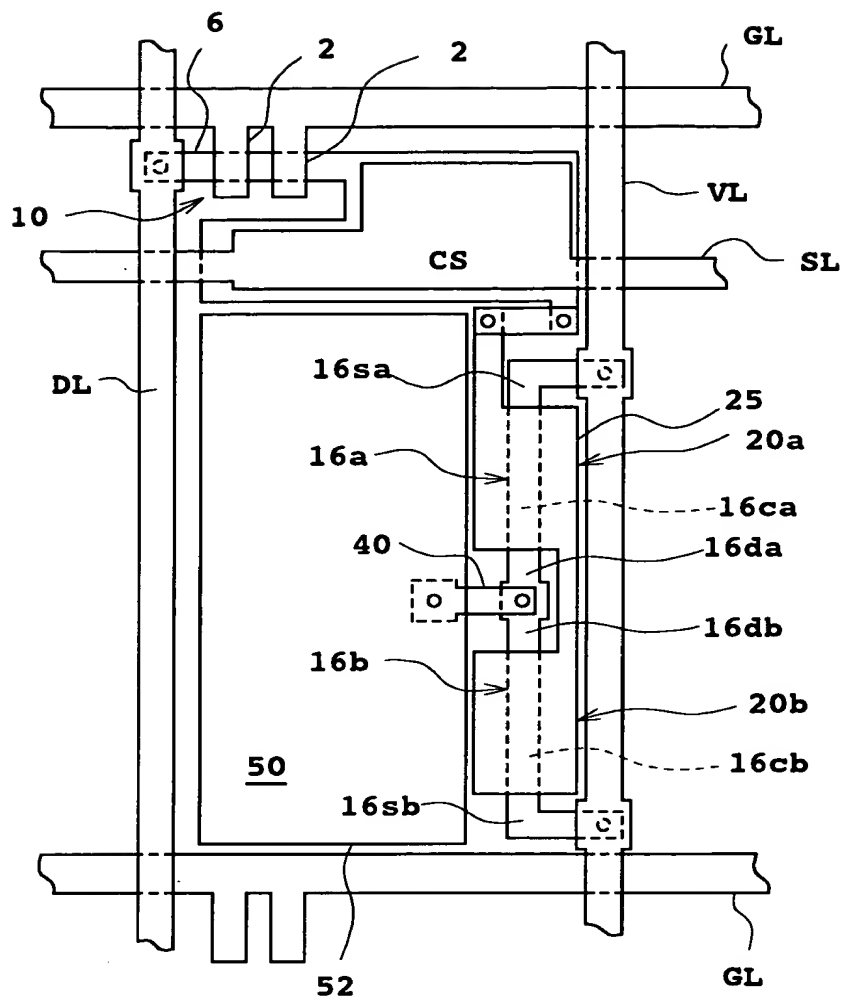


Fig. 12

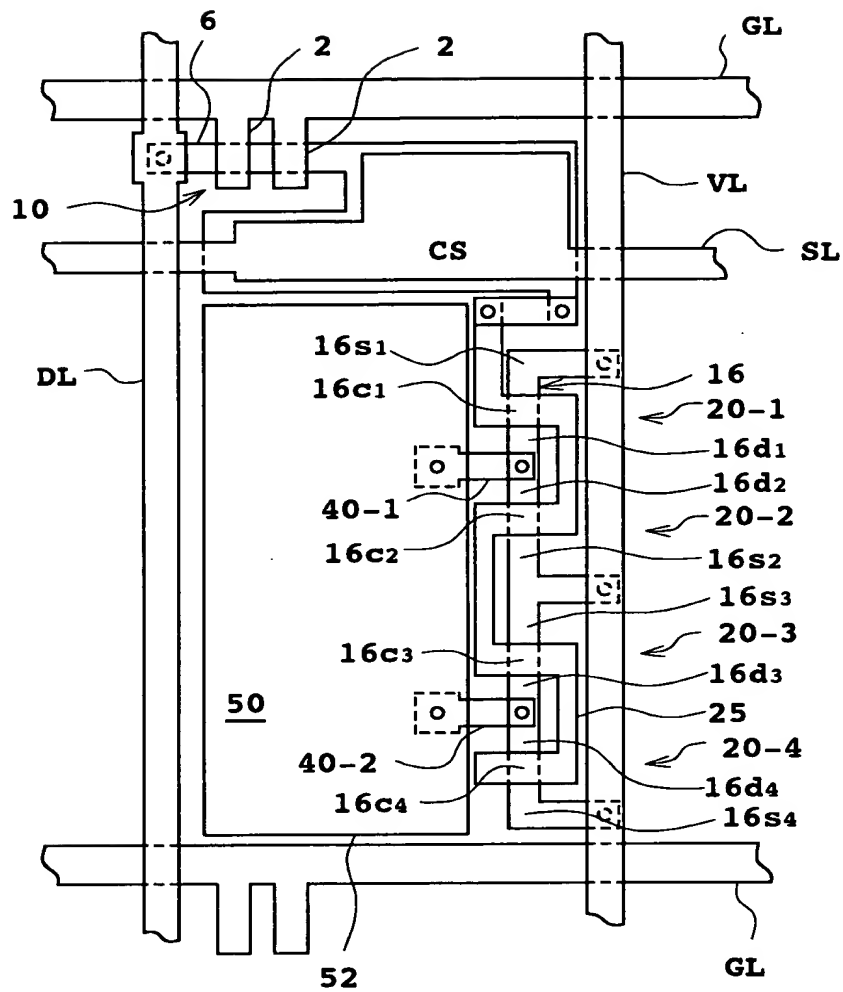


Fig.14

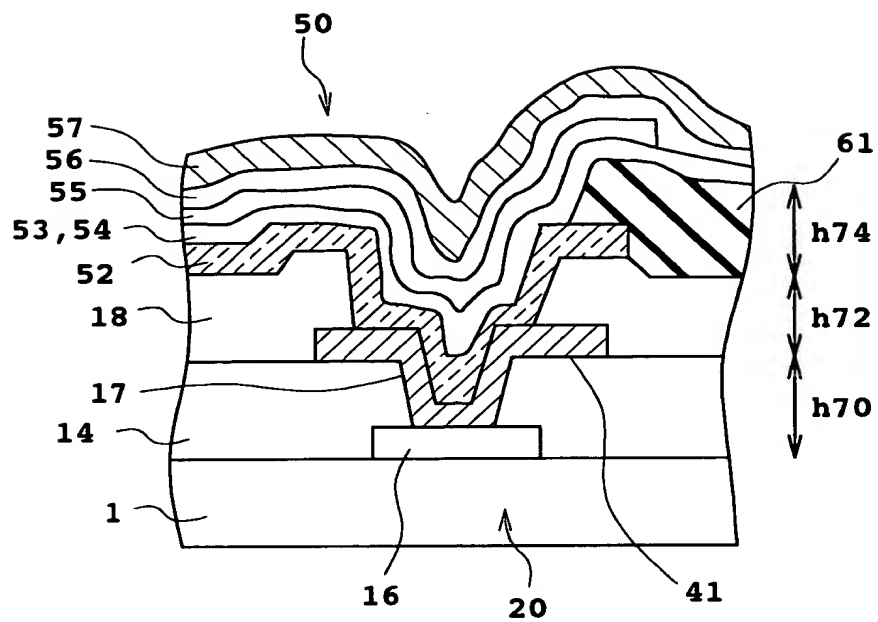


Fig. 15A

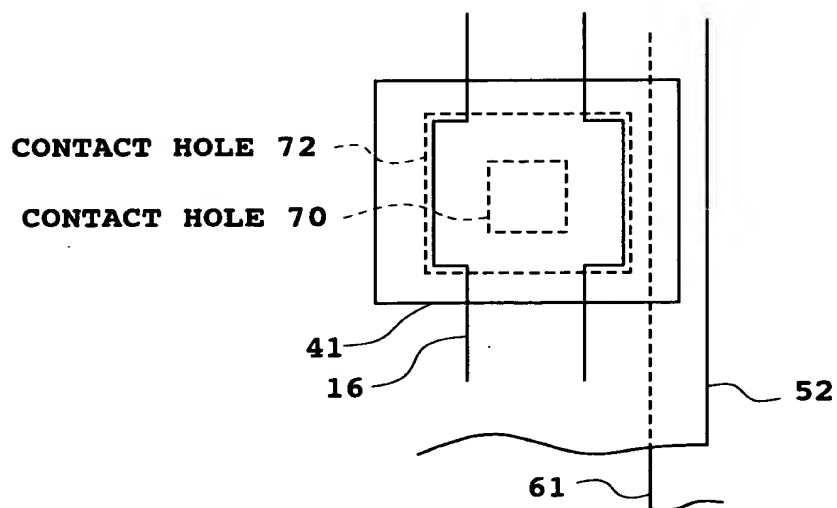


Fig. 15B

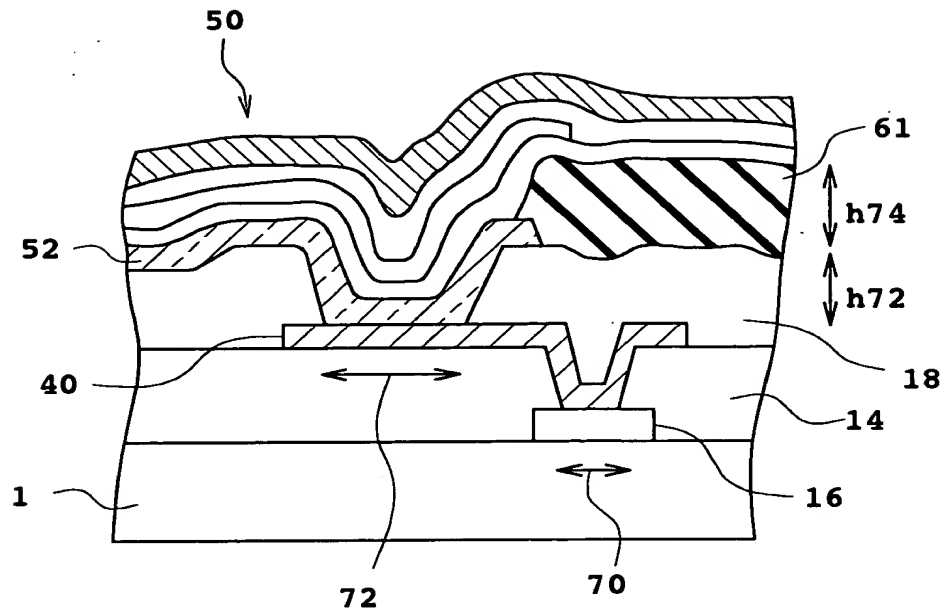


Fig.16A

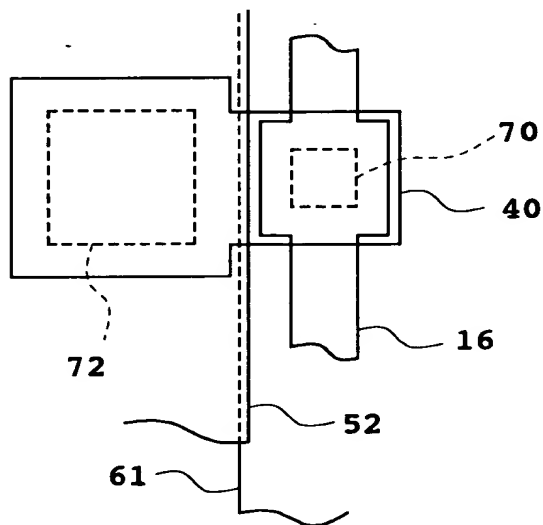


Fig.16B

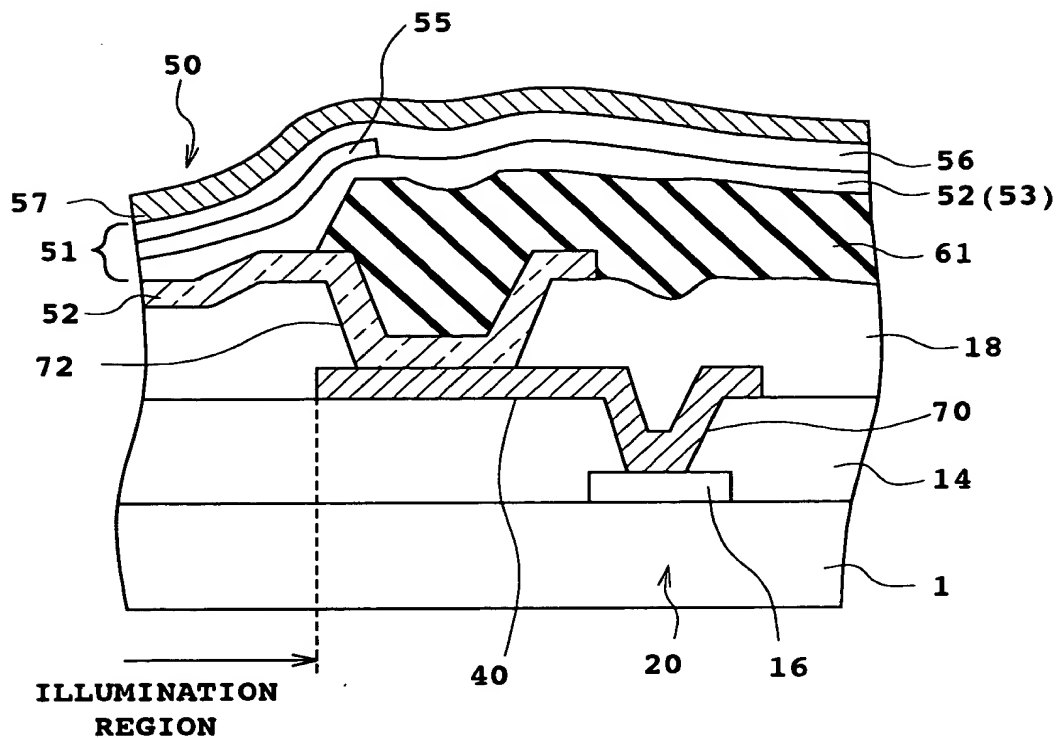


Fig. 17

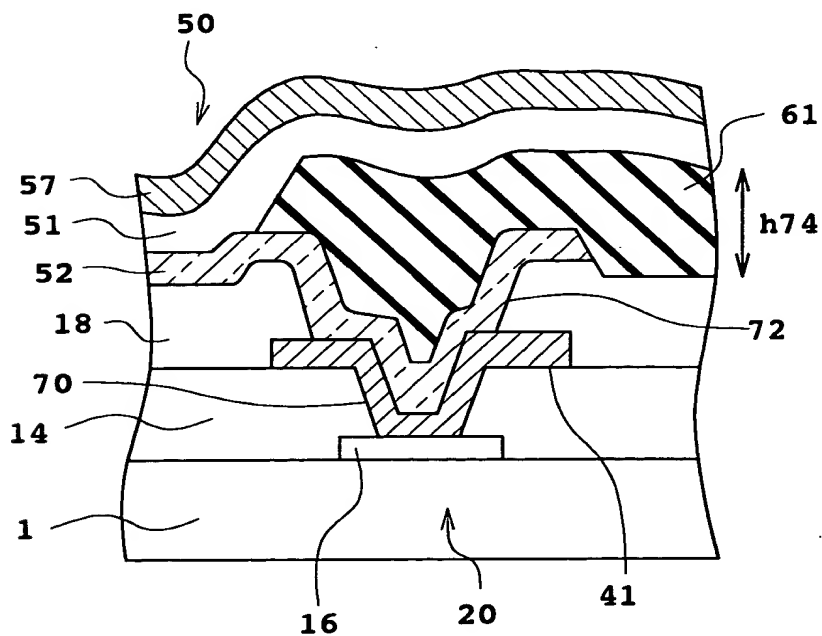


Fig. 18

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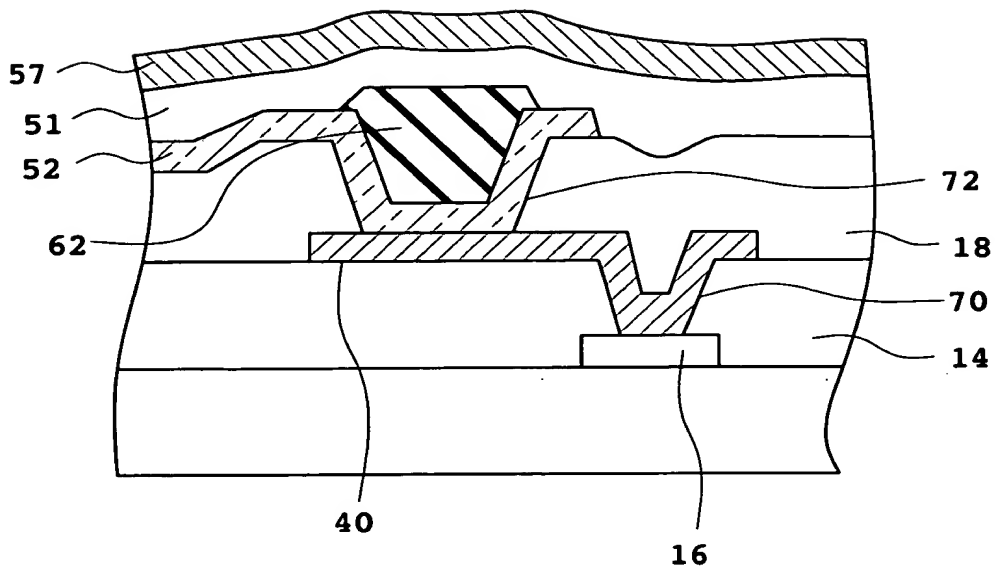


Fig.19

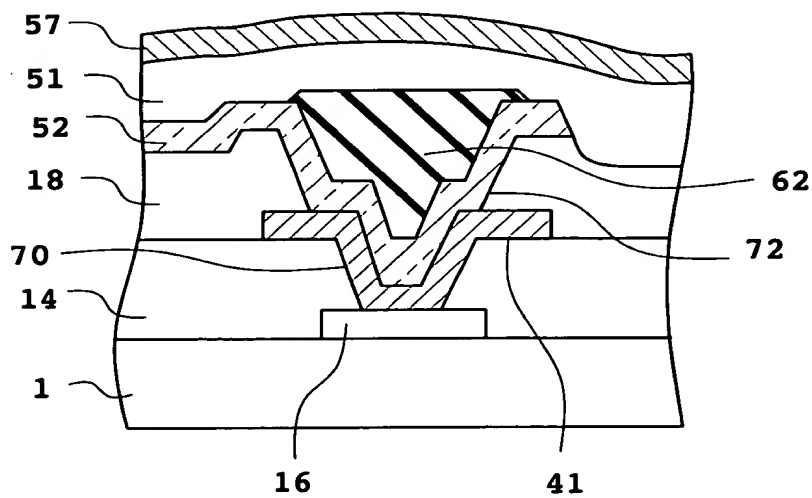


Fig.20